Nanocon ned Polystyrene: A New Phase

Sudeshna Chattopadhyay, A lokm ay Datta, Avijit Das Surface Physics Division, Saha Institute of Nuclear Physics, 1/AF, Bidhannagar, Calcutta 700 064. India.

Angelo Giglia, Stefano Nannarone, Nicola Mahne TASC-INFM, AREA Science Park, ss 14 Km 163.5, I-34012, Basovizza (TS), Italy

## A bstract

Transverse layering ofm olecular gyration spheres in spin-coated atactic polystyrene (aPS) Ims, for Im thickness R  $4R_g$  ( $R_g$  = unperturbed gyration radius), causes an increase in free energy that does not follow the ( $R_g$ =R) <sup>2</sup> dependence of planar connem ent and is explained by invoking a xed-range, repulsive, modiled Poschl-Teller intermolecular potential, its strength decreasing with increase in R. Vacuum ultraviolet spectroscopy reveals a change in 'physical dimers' of adjacent pendant benzene rings of aPS from 'oblique' to 'head-to-tail' conguration as Im thickness goes from  $9R_g$  to  $2R_g$ . This reduces cohesion by reducing dimer dipolem oment. Thus a new phase of aPS, the nanoconned phase, ordered but with lower cohesion than bulk, is formed.

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One-dimensional geometrical connement of uids causes the uid to form layers normal to the connement direction [1, 2, 3]. For such 'nanoconned' simple uids the layer periodicity is equal to the molecular size while for polymers (complex uids) it is equal to the unperturbed gyration radius ( $R_g$ ) [2], i.e., the dimension of a polymer molecule in the maximum entropy conguration [4]. Nanoconned uids exhibit radically new mechanical, thermal, dielectric and rheological properties [5, 6]. In a very recent study, a nanoconned simple liquid has been observed to be in a 'laterally cooperative' state that behaves liquid-like or solid-like depending on the kinematics of the measurement process [7]. In polymers layers form only when In thickness is less than  $4R_g$  and there is a reduction in cohesion between adjacent molecular gyration spheres [8], i.e. an increase in free energy. These new properties suggest a basic reorganization at molecular levels and they are bound to have strong implications in any technology employing thin uid In such as optoelectronic and magnetic coatings, adhesives, biological membranes and emerging nanotechnologies, in particular, photonics and nano uidics.

In this communication we show that the increase in free energy due to layering does not tally with that observed for planar con nement [9, 10]. We not, from tapping-mode atom ic force microscopy studies, a very similar con nement-induced reduction in cohesion between adjacent gyration spheres on the lm surface. We have explained this drop in cohesive interaction as the emergence of a new, repulsive intermolecular potential that the swell with a modiled Poschl-Teller potential (MPT) [11], whose depth can be increased by thinning the lm but whose range is invariant with con nement. We have also shown, through vacuum ultraviolet (vuv) spectroscopy, that con nement causes a change in the geometry of pairs ('physical dimers') of adjacent pendant benzene rings in polystyrene from 'oblique' to 'head-to-tail' that reduces the dipole moment of each 'dimer', which in turn, reduces cohesion between molecular gyration spheres.

Atactic polystyrene (aPS, mol. wt. M ' 560900,  $R_g=0.272 M^{\frac{1}{2}}$ ' 20.4 nm) [12] was spin-coated on fused quartz plates from toluene solutions using a photo resist spin-coater (Headway Inc.) to form Ims with thickness (R) varying from 40 nm ('  $2R_g$ ) to 180 nm ('  $9R_g$ ), and with air/ Im and Im/substrate interfacial roughness 0.6 nm, as has been described previously [8]. Contaminants are removed from the substrate by boiling it with 5:1:1 H  $_2$ O : H  $_2$ O  $_2$ : N H  $_4$ O H solution for 10 m inutes, followed by rinsing in acetone and ethyl alcohol.

A tom ic Force M icroscopy (AFM) im ages were acquired in tapping-m ode with N anoscope IV, Vecco Instruments, using etched Sitip and Phosphorus doped Sicantilevers. The free amplitude was  $A_0 = 36$  nm, set point amplitude A = 10.94 nm, cantilever quality factor Q = 505, resonance frequency  $l_0 = 2$  283 kHz and spring constant k = 20 Nm  $l_0 = 2$  283 kHz and spring constant  $l_0 = 2$  285 kHz and spring constant  $l_0 = 2$  286 kHz and spring constant  $l_0 = 2$  286 kHz and spring constant  $l_0 = 2$  287 kHz and spring constant  $l_0 = 2$  287 kHz and spring constant  $l_0 = 2$  288 kHz and spring constant  $l_0 = 2$  288 kHz and spring constant  $l_0 = 2$  289 kHz and spring constant  $l_0 = 2$  289 kHz and spring constant  $l_0 = 2$  289 kHz and spring constant  $l_0 = 2$  290 kHz and spri

Figure 1 (a) shows the re-ectivity pro-les (open circles) of aPS  $\,$  lm s of di-erent R-values, and the extracted EDPs from best  $\,$  ts (line) are shown in Figure 1 (b) in the same sequence and having the same color code. For R  $\,$  4R $_{\rm g}$  (84.0 nm) we observe form ation of layers in aPS parallel to the substrate surface, the error in  $\,$  being an order of magnitude less than this variation [2]. The reduction in cohesive energy caused by the variation of density due to layering is given by [8, 12, 13]

$$G_{PSPS}^{(o)} = A_{PS}^{(o)} = (2:1 \quad 10^{21})$$

$$= PS ((z)^2 \quad \frac{2}{max}) = (2:1 \quad 10^{21})$$
(1)

where  $G_{PSPS}^{(o)}$  is the reduction in (out-of-plane) cohesive energy caused by the variation of density due to layering,  $A_{PS}^{(o)}$  is the (out-of-plane) change in polystyrene H am aker constant, PS is the polarizability of aPS and PS and PS and PS denotes the electron density at depth PS (corresponding maximum).

Figure 1(c) shows the variation of A  $_{PS}^{(o)}$  with (R  $_{g}$ =R), obtained from Eqn (1). The continuous line is the best t to the data (open circles) with the function

$$A_{PS}^{(0)} = K (R_q = R)^b$$
 (2)

The value of b obtained from this t is 3.0 0.3. This deviates clearly from b = 2, for an ideal polymer, or from b = 1.7, for a self-avoiding polymer [9], under planar connement [10] and, rather, correspond to spherical connement [9] of the polymer. We are thus led to study the variation of surface free energy of the polymer lm s w ith R to inspect for any deviations from planar connement.

Figures 2(a) and 2(b) show the phase images obtained from tapping-mode AFM of two typical aPS lmswith R' 50.0 nm and 84.0 nm, respectively. The topographical images

of all these Ims show roughly spherical features with an average diameter of R $_g$  [8], corresponding to gyration spheres. The frusta (\* 0.6 nm high) of these spheres are consistent with the top roughness obtained from x-ray studies. But the phase images show larger variations in phase-shifts between adjacent 'spheres' on Imsurface as R reduces from 84.0 nm to 40.0 nm, implying a larger variation in energy dissipated by the AFM tip in going over from sphere to sphere [14] and, by extension, a spatial variation in surface free energy that increases with decrease in R. This spatial variation is not observed for R > 4R $_g$  and it cannot be explained by simple planar connement of the polymer. Thus, above a certain degree of connement, the very nature of connement is changed by the formation of layers. We have tried to indicate that exactly is changing in the Ims from the layering induced variations in free energy along Im-depth, presented above, and on Im-surface, discussed below.

To the end of determ in ing the variation in surface free energy caused by layering, we have estimated the average energy dissipated per cycle by the tip over the  $\,$ lm surfaces, E  $_{\rm D}$ , using the expression [14]

$$\sin = (\frac{!}{!_0} \frac{A}{A_0}) + \frac{Q E_D}{kAA_0}$$
 (3)

where is the phase-shift with respect to the drive signal and the other terms have been described above.

The tip exerts a van der W aals force on the surface, during approach and retraction. This interaction is modeled as a sphere approaching a plane with an elective contact area  $4\ r_{c\ Si}$ , where  $r_{c}$  is radius of tip-curvature (' 10nm) and Si is the Si atom ic diameter (= 0.22nm). Then energy dissipation by the tip in the Si lands with respect to minima is given by [12, 15]

$$E_{D} = \frac{2}{3} \frac{r_{CSi}}{z_{0}^{2}} A_{SiPS}$$
 (4)

where tip-sam ple adhesion, expressed by  $A_{SiPS}$  (the corresponding H am aker constant) is considered to be the varying interaction [15], which is una ected by cantilever tilt [16]. Here  $z_0$  is the tip-sam ple separation (' 0.2 nm in contact [12]). Using the expression  $A_{SiPS} = A_{Si}^{\frac{1}{2}}A_{PS}^{\frac{1}{2}}$  [17], where  $A_{Si}$  and  $A_{PS}$  denote the H am aker constants of Si and aPS respectively, along with Eqns (3) and (4), the value of  $A_{Si}$  [17] and some simple algebra, we determ ine  $A_{PS}$ , the in-plane variation in aPS H am aker constant and hence  $G_{PS}$ , the

(in-plane) variation in cohesion.

Figure 1 (d) shows the observed variation (in solid circles) of  $G_{PSPS}^{(o)}$  with depth z across the gap between adjacent layers, for all the dierent R-values probed. Similarly, Figure 2 (c) depicts  $G_{PSPS}^{(i)}$  variation (solid circles) over adjacent gyration spheres as a function of in-plane coordinate x, for dierent lm thicknesses. In both cases the abscissae have been shifted arbitrarily for clarity. It is interesting to note that in all cases  $G_{PSPS}$  shave a form that ts very well with the MPT potential given by [11]

$$G_{PSPS}$$
 ( ) =  $V_0 \cosh^2 = g^2 \cosh^2$  (5)

Here  $V_0$  is the peak strength of the repulsive intermolecular potential, which has a quadratic dependence on =  $^1$ , being the range of the potential (at = 2, V = 0.07V $_0$ ), and  $g^2$  has the dimension of energy. The best tourves of data with the MPT potential are shown in continuous lines in Figures 1 (d) and 2 (c) and values of  $V_0$  and obtained from these ts are given in Table 1. From this table it is clear that connement has introduced an additional intermolecular potential whose magnitude, given by  $V_0$ , increases as In thickness is decreased but whose range remains more-or-less invariant. It should also be noted that, for a In with thickness >  $4R_g$  the in-plane potential is measurable but very small, consistent with the out-of-plane measurements. The situation is depicted in the cartoon in Figure 2 (d).

In order to correlate this new interm olecular potential with some special change in the molecular conguration of aPS, we have carried out vuv spectroscopy of polystyrene. In swith R'  $2R_g$  and R'  $9R_g$ . Transmission spectra in the 4-9 eV range were collected in 10 m eV steps at BEAR beam line of ELETTRA synchrotron, with nearly linearly polarized light (the estimated Stokes parameter  $S_1$ ' 0.5), the electric eld lying in the Implane [18]. The experimental chamber was maintained at  $10^{10}$  Torrand all measurements were done at ambient temperature. Our focus was on the pure electronic singlet transition  $^1A_{1g}$ !  $^1E_{1u}$  involving the pendant benzene rings of aPS, which is centered around 6 eV.

Figures 3 show this spectral band for 180.0 nm (a) and 50.0 nm (b) thick aPS lm s. The split in the band can be explained as arising from the resonant transfer interaction between correlated clusters of pendant benzene rings, given by J = 2' 428 m eV, where is the measured split [19], which causes the mixing of the singly excited states of individual benzene rings through their transition dipole moments. The doublet splitting indicates

that 'dim ers' of benzene rings are involved in these clusters. The intensity ratio of the high energy (+) and low energy (+) components of the doublets,  $I_+ = I_- = (1 + \cos_-) = (1 - \cos_-) = \cot_-^2(-2)$  gives , the angle between the transition dipoles, i.e. the dihedral angle between rings of the 'dim er' [20], since the transition dipole is entirely in the ring-plane. The strong electronic band gives a clear indication of the change in the value of between the two lms from the change in intensities of these components. goes from '75 to' 0 as lm thickness goes from 180.0 nm to 50.0 nm, corresponding to an 'oblique' or ob conguration (shown schematically in inset, Figure 3(a)) and a 'head-to-tail' or ht conguration (inset, Figure 3(b)) [19], respectively. A benzene 'dim er' has a permanent dipolem oment only when rings are non-parallel [21], hence the ht 'dim er' will have near-vanishing dipole moment. This would make it undetectable through standard spectroscopic techniques [21] and to our knowledge this is the rst direct experimental evidence of this 'near-parallel' benzene 'dim er'. Reduction in 'dim er' dipole moment due to this congurational change would reduce coupling between gyration spheres containing such 'dim ers'. We suggest that this is manifested as the repulsive MPT intermolecular potential.

We have found a completely new phase of atactic polystyrene under connement – the nanoconned phase, more ordered than the (inherently disordered) bulk but less cohesive. Observation of similar phases in a simple uid [3] indicates the universality of this phase and also shows a limit to which simple and complex uids have the same behavior. We show here that in aPS this phase is achieved through the alignment of adjacent benzene rings, explaining the similarity of conned aPS to the helically ordered phases of syndiotactic PS, observed in infrared spectra [22]. The contradictory properties of this phase may explain its other observed properties, in particular its solid-liquid duality [7], reduction of  $T_g$  with connement and its dependence on  $R_g$ , and return to bulk  $T_g$ -value on adding small-molecule diluents [6, 23]. This phase would also usher in new concepts in miscibility and solvation.

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## Figure captions

FIG. 1: (color online) (a): X-ray re ectivity data (circles, Fresnel re ectivity normalized and upshifted) and ts (lines) of polystyrene (PS) Ims on quartz with dierent thicknesses R (shown beside each curve). (b): Electron Density Proles (EDPs) along Im depth from relectivity ts, color-coded and presented in same sequence. (c): A  $_{PS}^{(o)}$ , increase in free energy due to layering, versus (R  $_{g}$ =R), R  $_{g}$  = unperturbed gyration radius of PS (20.4 nm). Circles: data, Line: best twith K (R  $_{g}$ =R) $_{PS}^{(o)}$ , variation of cohesion versus depth z, for R-values shown. Circles: data, Line: best twith modiled Poschl-Teller (MPT) function. Curves side-shifted for clarity.

FIG. 2: (color online) Phase images of tapping-mode Atomic Force Microscopy (AFM) scans (500nm 500nm) of PS lm s w ith R = 50.0 nm ('  $2R_g$ )(a) and 84.0 nm ('  $4R_g$ )(b). (c):  $G_{PSPS}$ , variation of cohesion versus in-plane co-ordinate x, for dierent R-values shown. Circles: data, Line: best twith MPT function. Curves have been side-shifted for clarity. (d): Schematic of the connect system.

FIG. 3: (color online) Transm ission spectra (absorbance versus photon energy) in vacuum ultraviolet (vuv) for PS  $\,$  lm s w ith R = 180.0 nm (a) and 50.0 nm (b). A ssigned transitions presented beside spectralbands. C ircles: data, red line: convolution of individual gaussian  $\,$  ts (only those for 'dim er' peaks shown in green). Inset: C on gurations of benzene 'dim ers' extracted from analysis of  $^{1}A_{1g}$ !  $^{1}E_{1u}$ . = dihedral angle.

TABLE I: Param eters of the interm olecular potential

Film	Peak strength		R ange	
Thickness	$(V_0)$ (m J m $^2$ ) from		()(nm)from	
(nm )	XR a	AFM	ΧR	AFM
114	0	1.42	0	5 <b>.</b> 6
84	1 <b>.</b> 97	3. <b>2</b> 9	5 <b>.</b> 9	6.5
60.4	3.36	3 <b>.</b> 47	5.3	5.1
58.5	3 <b>.</b> 73	-	4.8	-
52	4.68	-	6 <b>.</b> 4	-
50	5.36	6.37	5.3	5.3
48.5	5 <b>.</b> 95	_	5.3	-

aX -ray Re ectivity